



Zero Recovery Silicon Carbide Schottky Diode

PRODUCT APPLICATIONS

- Anti-Parallel Diode

 Switchmode Power Supply
 Inverters
- Power Factor Correction (PFC)

PRODUCT FEATURES

- Zero Recovery Times (t_{rr})
- Popular TO-247 Package or surface mount D³PAK package
- Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Higher Reliability Systems
- Minimizes or eliminates snubber



1 - Cathode 2 - Anode Back of Case - Cathode

MAXIMUM RATINGS

 T_C = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions		Ratings	Unit	
V _R	Maximum D.C. Reverse Voltage			Volts	
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		1200		
V _{RWM}	Maximum Working Peak Reverse Voltage				
I _F	Maximum D.C. Forward current	T _C = 25°C	68		
		T _c = 135°C	20		
I _{FRM}	Repetitive Peak Forward Suge Current (T _J = 45°C, t _p = 10ms, Half Sine Wave)		100	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current (T _J = 25°C, t _p = 10ms, Half Sine)		220]	
P _{tot}	Power Dissipation	T _C = 25°C	208	W	
		T _c = 110°C	66		
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to 150	- °C	
T_L	Lead Temperature for 10 Seconds		300		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		Min	Тур	Max	Unit
$V_{_{\rm F}}$	Forward Voltage	I _F = 20A T _J = 25°C		1.5	1.8	Volts
		I _F = 20A, T _J = 150°C		2.2		
I _{RM}	Maximum Reverse Leakage Current	V _R = 1200V T _J = 25°C			400	μА
		V _R = 1200V, T _J = 150°C			2000	
Q _c	Total Capactive Charge V_R = 800V, I_F = 20A, di/dt = -100A/ μ s, T_J = 25°C			66		nC
С _т	Junction Capacitance $V_R = 0V$, $T_J = 25^{\circ}C$, $f = 1MHz$ Junction Capacitance $V_R = 200V$, $T_J = 25^{\circ}C$, $f = 1MHz$			1135		pF
				160		
	Junction Capacitance V _R = 400V, T _J = 25°C, f = 1MHz	:		100		

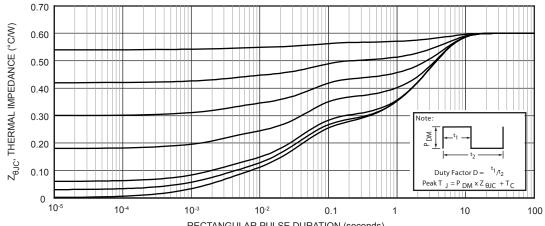
Microsemi Website - http://www.microsemi.com

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Тур	Max	Unit
R _{eJC}	Junction-to-Case Thermal Resistance			0.6	°C/W
W _T	Package Weight		0.22		OZ
			5.9		g
Torque	Maximum Mounting Torque			10	lb∙in
				1.1	N·m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES



RECTANGULAR PULSE DURATION (seconds)
FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

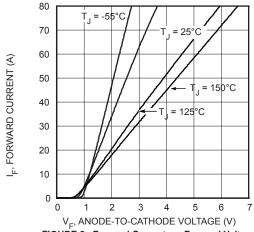


FIGURE 2, Forward Current vs. Forward Voltage

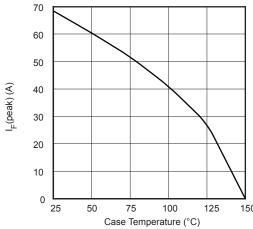


FIGURE 3, Maximum Forward Current vs. Case Temperature

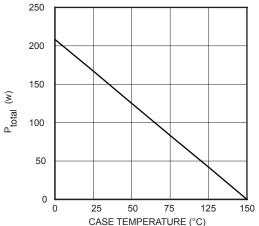
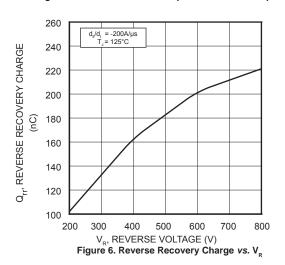


Figure 4. Maximum Power Dissipation vs. Case Temperature



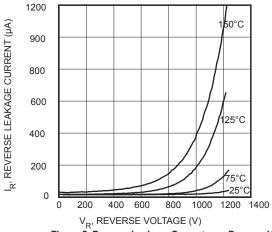
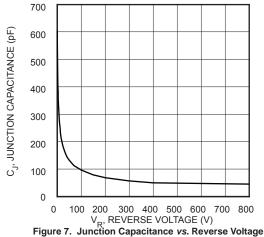
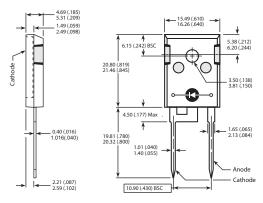


Figure 5. Reverse Leakage Currents vs. Reverse Voltage

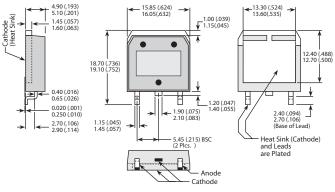


TO-247 Package Outline



Dimensions in Millimeters and (Inches)

D³PAK Package Outline



Dimensions in Millimeters and (Inches)

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